

Mystical source of electrically active chlorine at Cl doped CdTe

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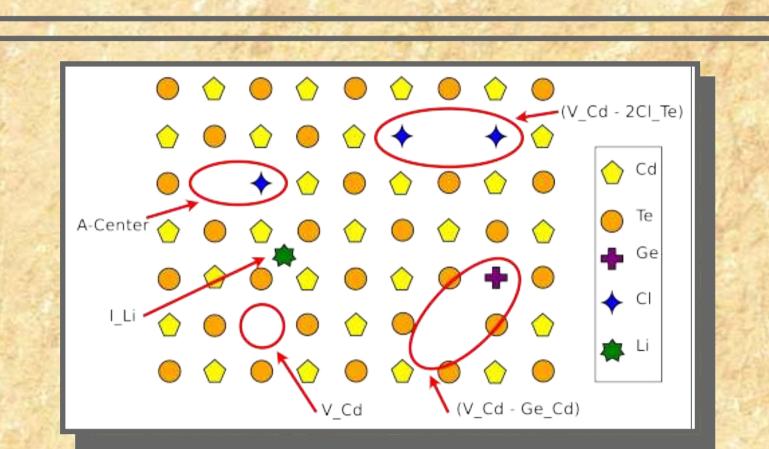
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1. Highlights

- Properties of Cd vacancy (V_{Cd}) represent a big puzzle in the CdTe research. Despite big effords in investigating its basic properties (e.g. formation and ionisation energies) in the last 50 years, it still remains undisclosed.
- In this presentation we study properties of V_{Cd} in CdTe doped by Cl (CdTe:Cl).
- The linear shape of the concentration curves can be explained by activation of electrically neutral chlorine at high temperatures.
- Direct experimental confirmation of the effect of annealing to the vacancy in CdTe.
- All visible vacancies are coupled with donors-like defects $(V_{Cd}-X_D)$ or $(V_{Cd}-2X_D)$.

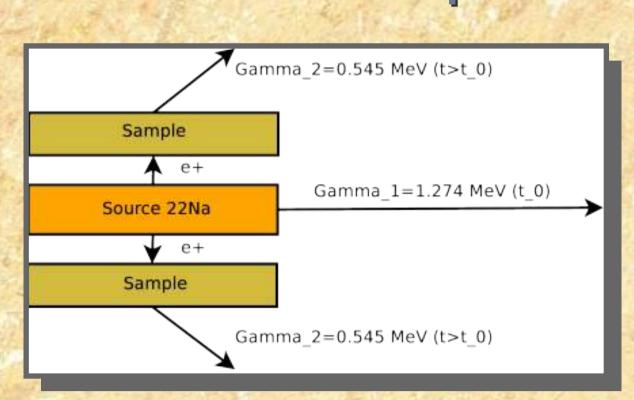
2. Point defects

- Vacancies
- Intersticials
- A-centers (V_{Cd}-X_D)
- Neutral $(V_{Cd}-2X_D)$



4. Positron - Experiment and Theory

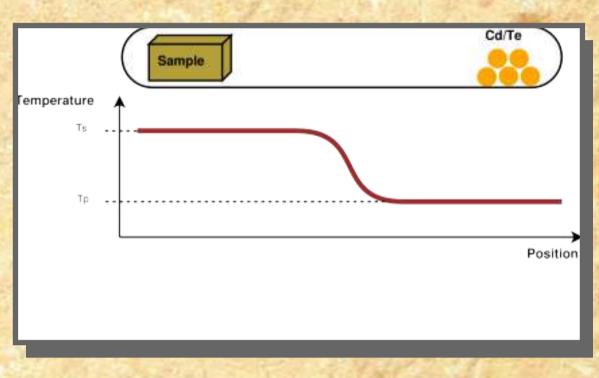
Positron annihilation spectroscopy



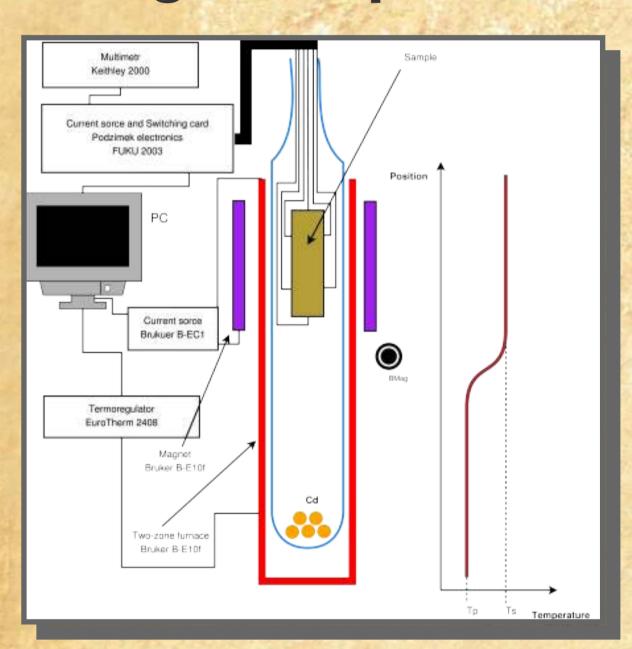
Annealing

- 1. Cd overpressure (700/600)
- 2. Te overpressure (700/600)

Chemical Analysis (GDMS)

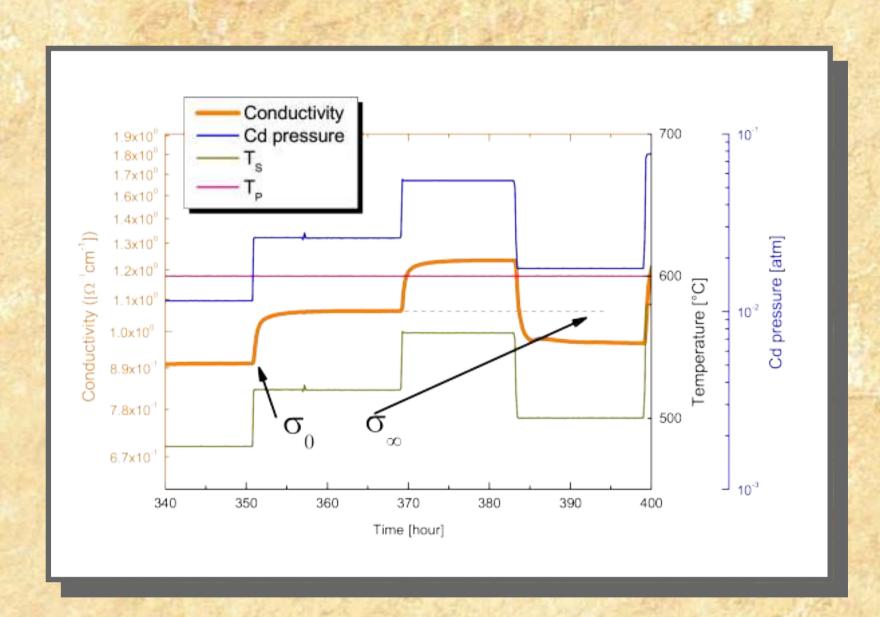


3. High temparature Hall effect



5. HT Hall effect - Results

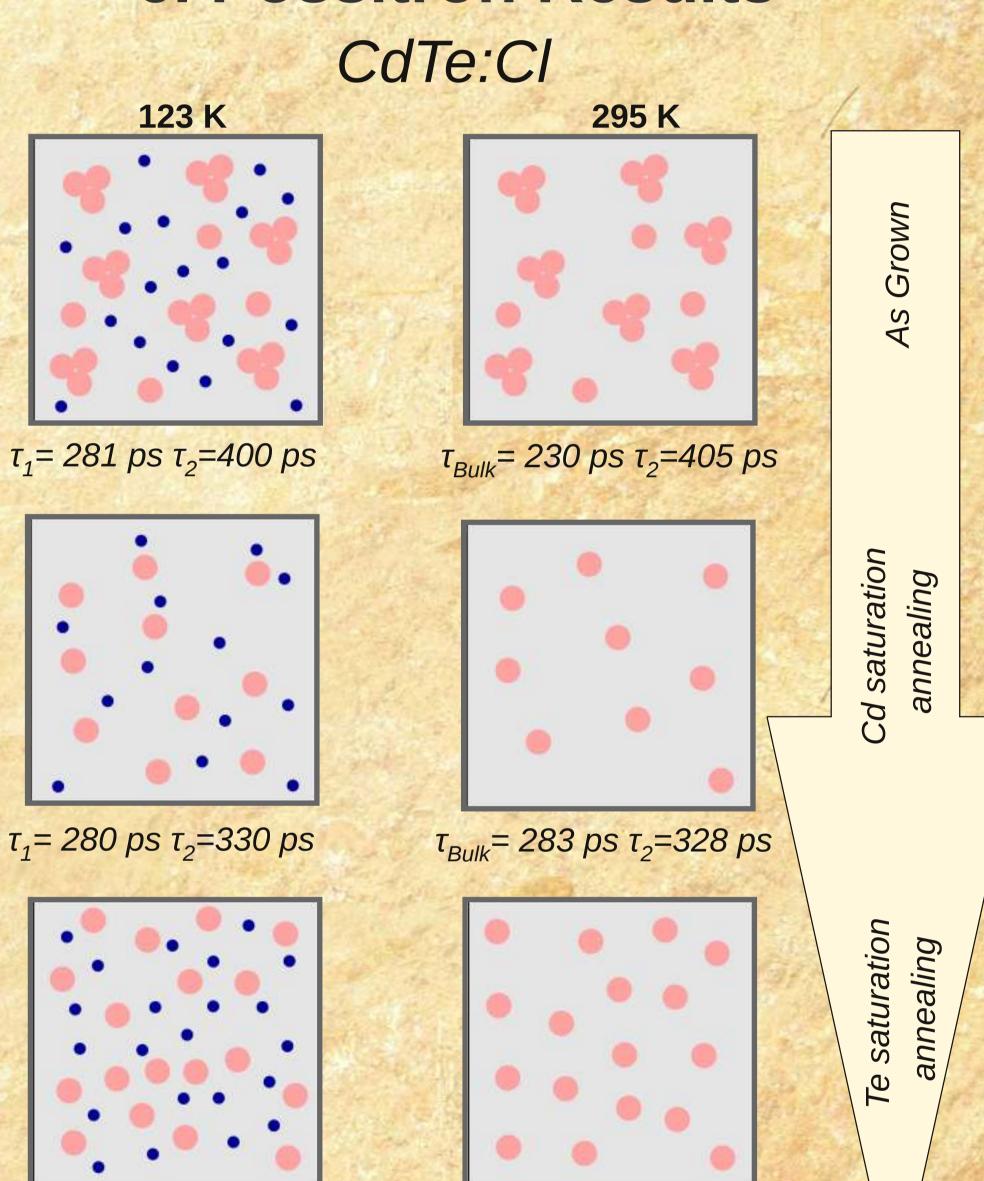
Corr. Data 600°C



7. Discussion

- CdTe:Cl contains temperature activated shallow defects, which are major defects at low temperature (123 K) Rydberg states around chlorine Accenters.
 The CdTe:Cl contains also
- The CdTe:Cl contains also neutral defects (V_{Cd}2Cl₂) grouped.
- The concentration of defects mentioned above decreses during annealing at Cd overpressure and increases after Te annealing.
- Dissolution of neural defects
 (V_{Cd}2Cl₂) and chlorine A centers is assumed to explain
 non standard shape of HT
 concentration curves.

6. Possitron Results



Shallow defects Rydberg states bound to the A-centers

Cluster of Neutral defects

Neutral defects

 $\tau_1 = 278 \text{ ps } \tau_2 = 320 \text{ ps}$

 $(V_{Cd}2Cl_2)$.

 $\tau_{Bulk} = 240 \text{ ps } \tau_2 = 316 \text{ ps}$

 $(V_{Cd}2Cl_2)$

- The CdTe:Cl contains neutral defects ($V_{\rm Cd}$ 2Cl₂) grouped in clusters.
- The CdTe:Cl contains Rydberg states bound to chlorine A-centers visible in low temperature.
- Annealing CdTe:Cl at Cd pressure decreases the density neutral defects (V_{Cd} 2Cl₂) and chlorine A-centers.
- Reannealing CdTe:Cl at Te pressure restorated Cd vacancies forming single A-centers.

The experimental data does not follows the standard model, the declination of experimental curves are not connected with interstitial concentration even at high pressure. This effect cannot be explained without

 $n \approx \left[Cd_I^{2+} \right] \approx p_{Cd}^{\frac{1}{3}}$

 This effect cannot be explained without some temperature activated defect, probably connected with chlorine.

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Summary

- The effect of annealing at CdTe:Cl was presented. Cd annealing leads to decrease of the density of Cd vacancies and A-centers and Te annealing restores these defects.
- First consistent interpretation of independent methods: positron spectroscopy, room temperature alvanomagnetic measurements, Glow Discharge Mass Spectrometry and theoretical calculation in CdTe:Cl.
- Simultaneous application of these methods enabled us to link directly the changes of electrical properties and development of point defects.
- CdTe:Cl contains temperature activated Rydberg states around chlorine A—centers, which are major defects
 at low temperature and this dissolution could be explanation for non standard shape of concentration curves.

References

1. KRAUSE-REHBERG, R., et al.: Review of defect investigations by means of positron annihilation in II-VI compound semiconductors. Applied Physics A: Materials Science. 1998-6-1, vol. 66, issue 6, p. 599-614.